

substance: titanium oxide (TiO₂)

property: physical properties of anatase

energy gap

E_g 3.23 eV 80G

Real and imaginary parts of the refractive index: Fig. 2. Optical absorption spectrum: Fig. 1.

defects

Very little systematic work has been reported on defects in anatase; evidence has however been adduced to support the argument that defects similar to the "A" centre in rutile can be formed on irradiation [77M].

phonon wavenumbers

Under the space group D_{4h}^{19} the local site vibrational fundamentals transform as $a_{1g} + a_{2u} + 2b_{1g} + b_{2u} + 3e_g + 2e_u$, of which a_{1g} , b_{1g} , and e_g are Raman active.

(in cm^{-1} , RT values)

ν/c	144 vvs	Mode: e_g	w: weak, m: medium,	67B
	144		s: strong, vs: very strong	78O
	197 w	e_g	Weak second order peaks also	67B
	197		seen at 316,696 and 796 cm^{-1}	78O
	400 m	b_{1g}	[67B]. The e_g band at 197 cm^{-1}	67B
	399		is considerably softened from	78O
	515 mw	b_{1g}	the value reported from a	67B
	513		rigid-ion calculation [79K];	78O
	519 mw	a_{1g}	for temperature dependence,	67B
	519		see Fig. 3, for pressure dependence,	78O
	640 m	e_g	see Fig. 4	67B
	639			78O

Above 25.6 kbar a transition to a new form of TiO₂ is observed which may have the PbO₂ or CaCl₂-structure [79O]. A similar transition has been reported for rutile.

transport properties

Resistivities of as grown crystals very variable: $10^4 \dots 10^{12} \Omega \text{ cm}$ [78V] at RT. Some typical data are shown in Fig. 5. For the more conducting samples two regions of behaviour are found: for $T > RT$, $\log \rho \propto E_A/kT$, where $E_A \approx 0.38 \text{ eV}$. For $T < RT$, random hopping behaviour is found, with $\log \rho \propto (T_0/T)^{1/4}$ and $T_0 \approx 22 \text{ K}$ [78V].

References:

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Fig. 1.

TiO₂, anatase and rutile. Low resolution spectra (optical density vs. wavenumber) [58B].

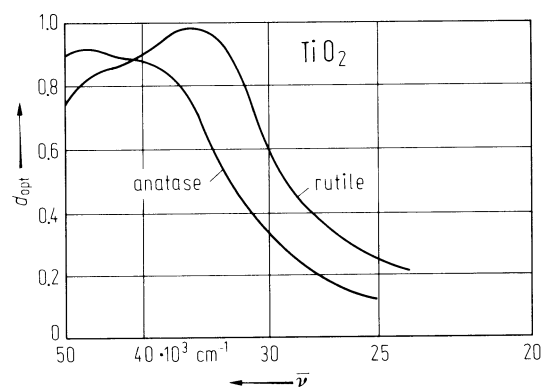


Fig. 2.

TiO₂. Optical properties of anatase films grown anodically on Ti metal in 1 N sulfuric acid [77B].

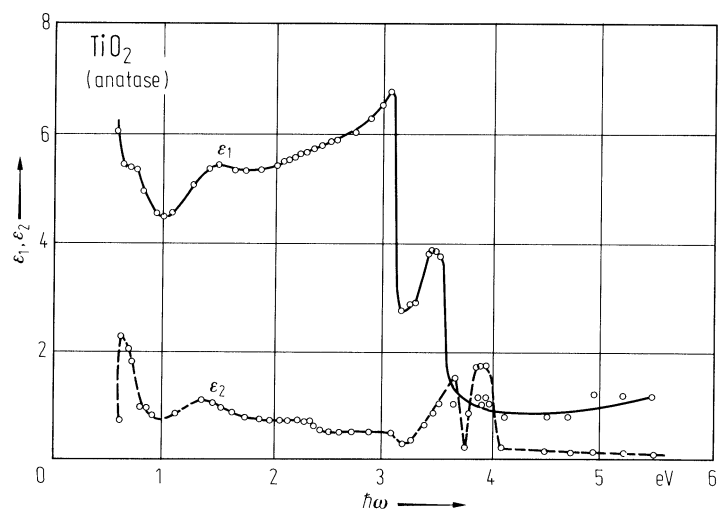


Fig. 3.

TiO₂. Raman shift vs. temperature for anatase modification [78O].

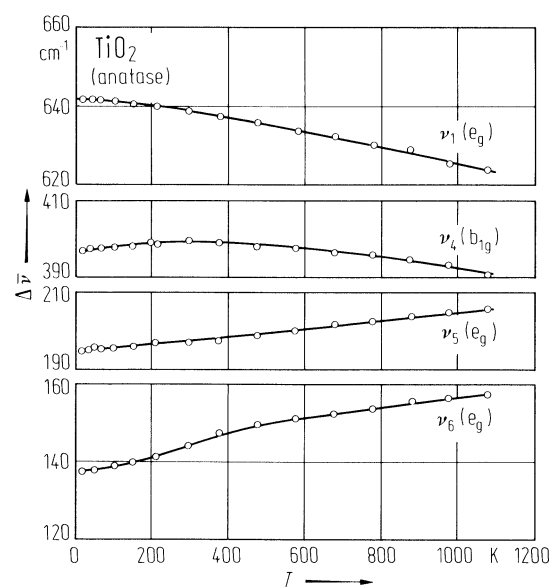


Fig. 4.

TiO₂. Raman wavenumbers vs. pressure at 298 K for anatase modification [78O].

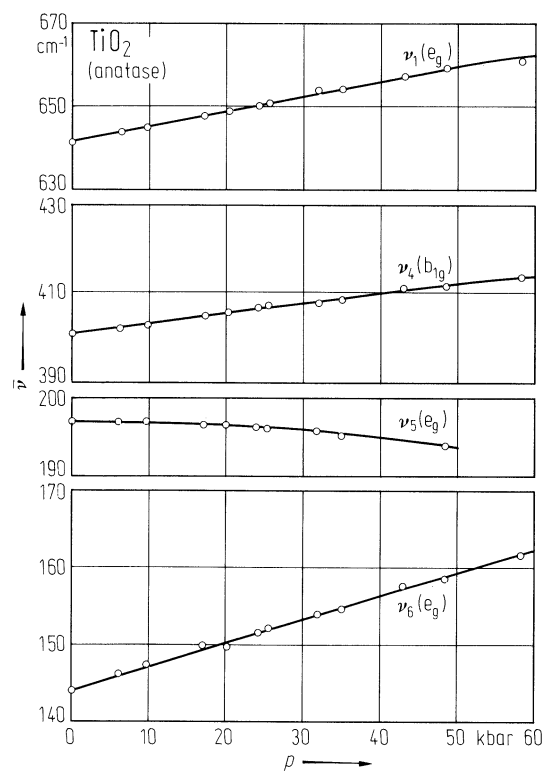


Fig. 5.

TiO_2 . Electrical resistivity of anatase modification vs. temperature. Curves 1...3: ρ vs. $10^3/T$ for three (unoriented) samples of differing dopant level; curves 1', 2': ρ vs. $(1/T)^{1/4}$ for the two (unoriented) samples of lower resistivity [78V].

